

Fabrication of micrometer-sized conical field emitters using femtosecond laser-assisted etching of silicon

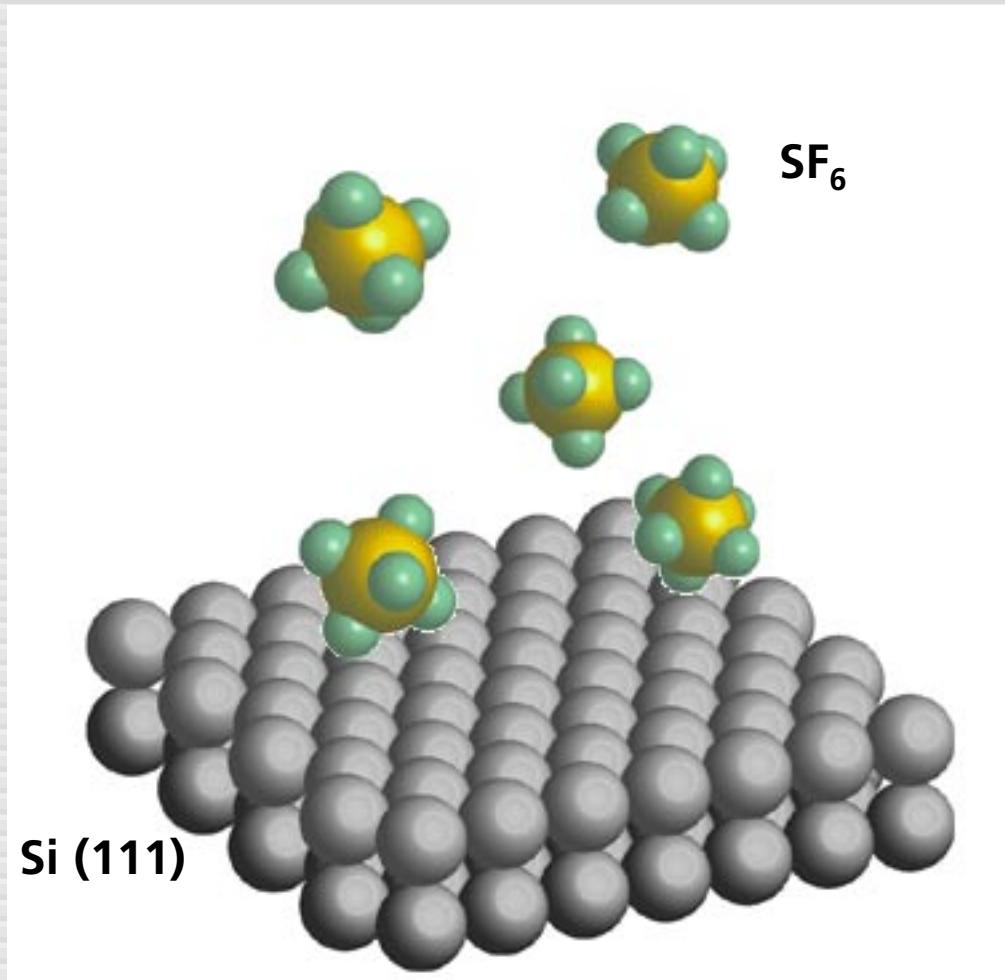
**Jim Carey
Catherine Crouch
Rebecca Younkin
Mike Sheehy
Li Zhao
Eric Mazur**



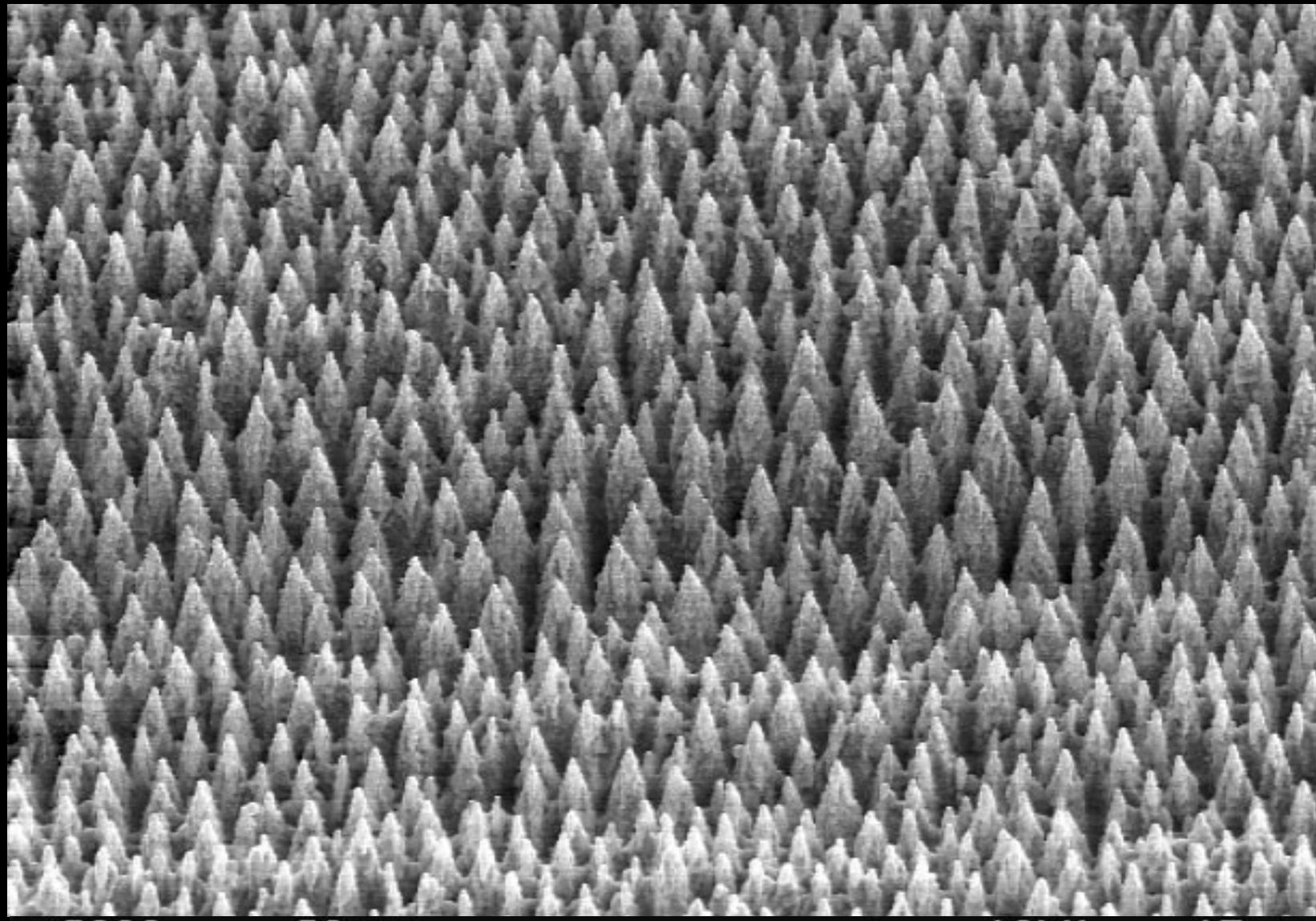
Outline

- ▶ **Background**
- ▶ **Results**
- ▶ **Discussion**

Background



irradiate with 100-fs $10\ kJ/m^2$ pulses



x2000

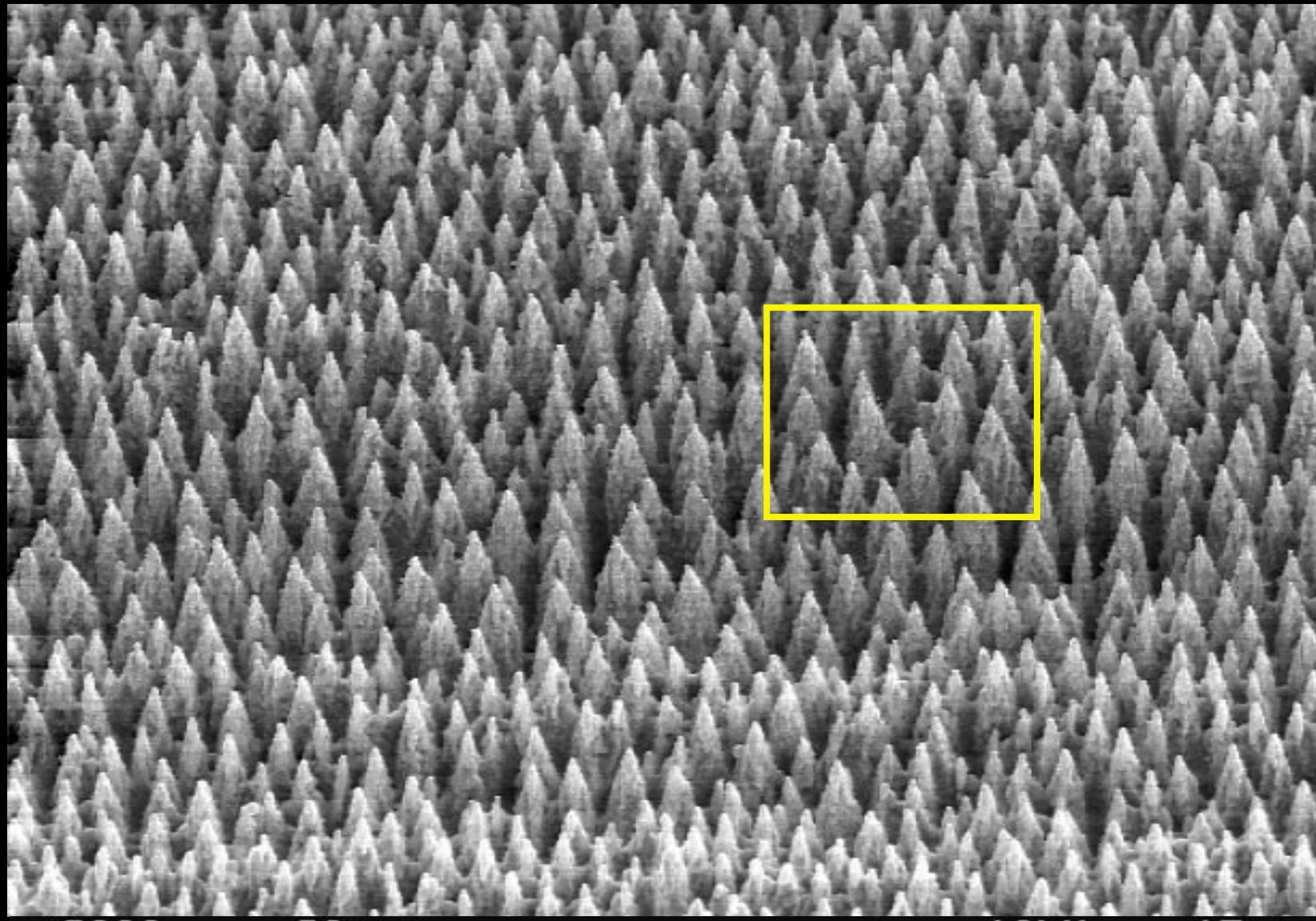
20 μm

#3548

512 x 480

10kV

15mm

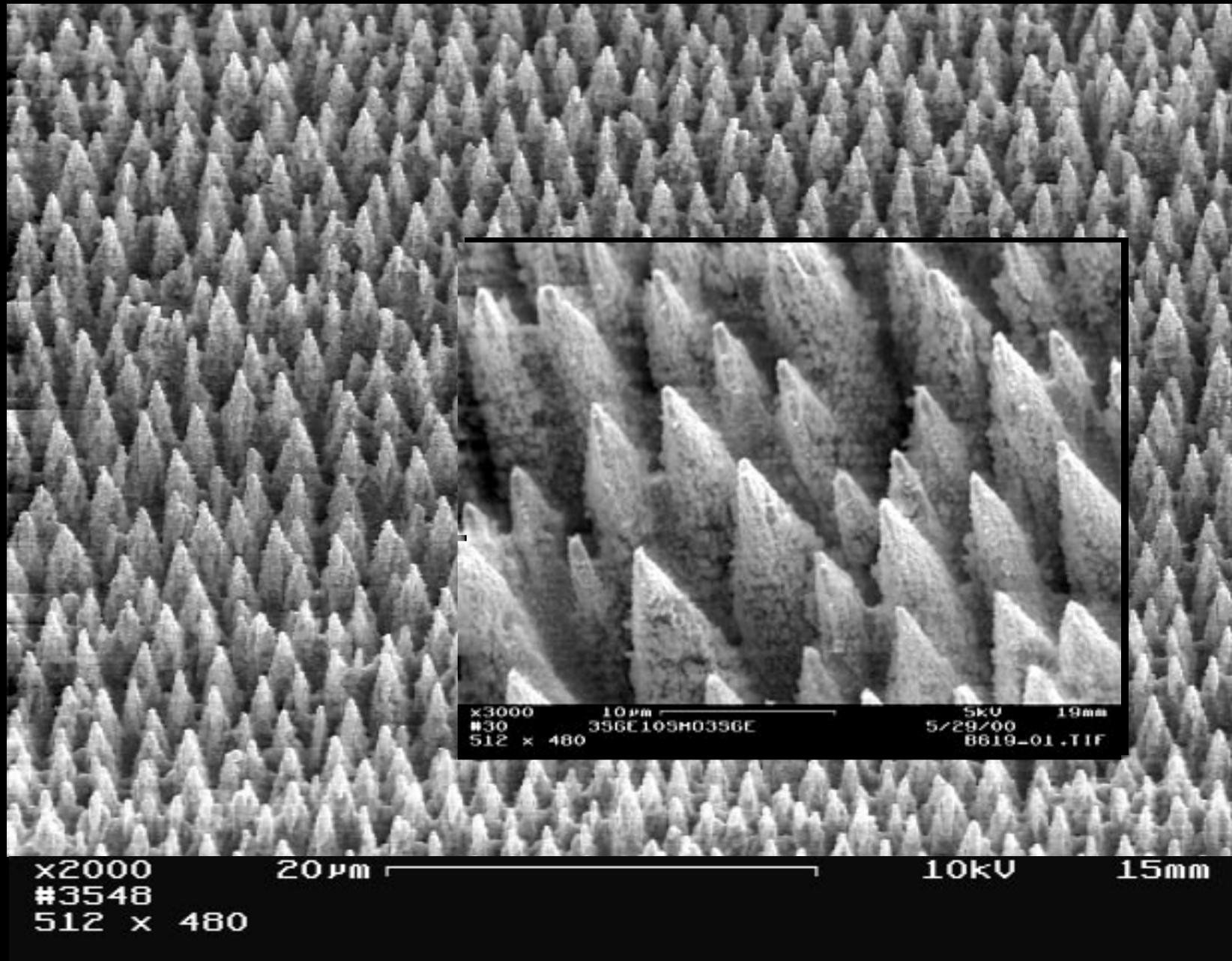


x2000
#3548
512 x 480

20 μm

10kV

15mm



x2000
#3548
512 x 480

20 μm

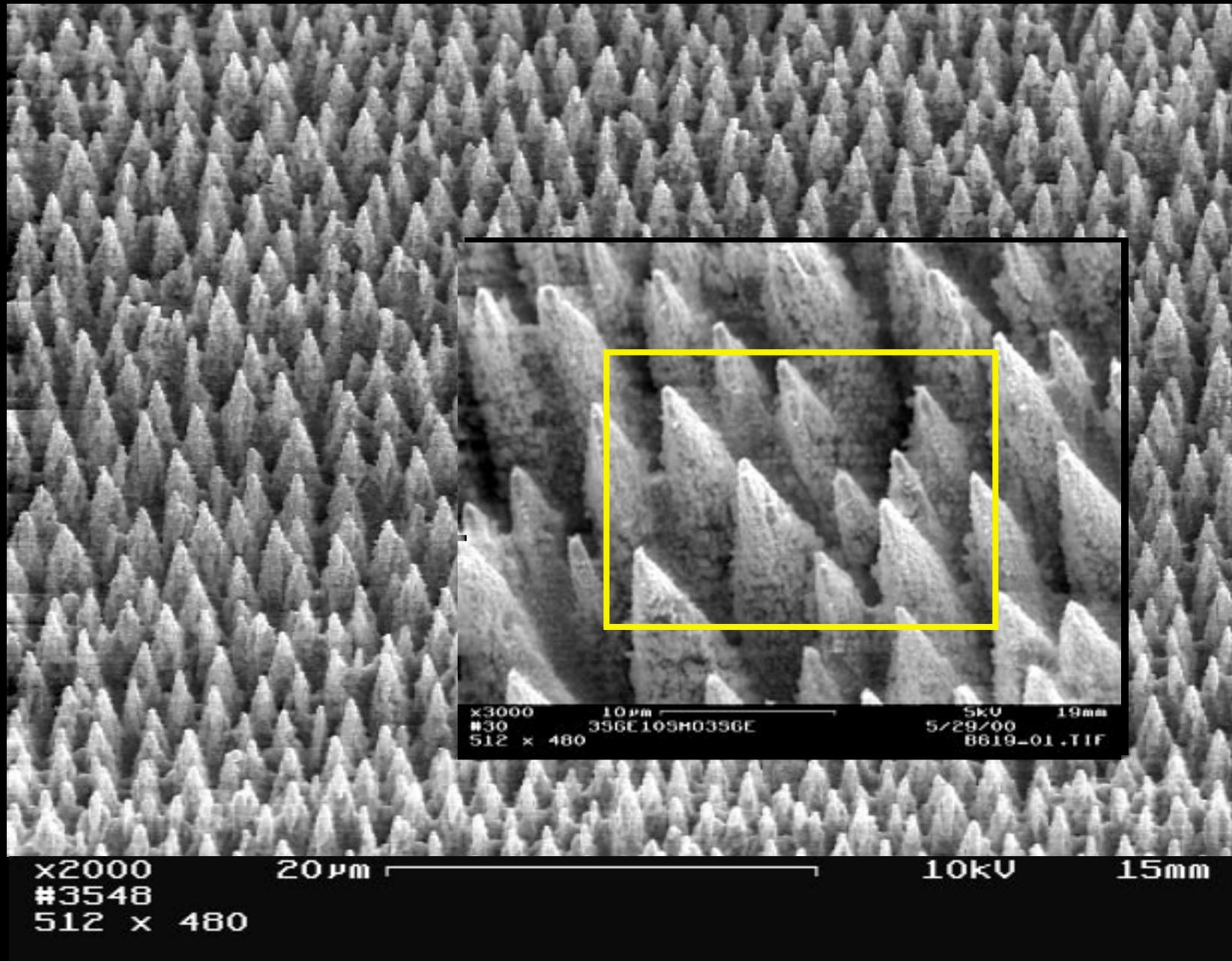
x3000
#30
512 x 480

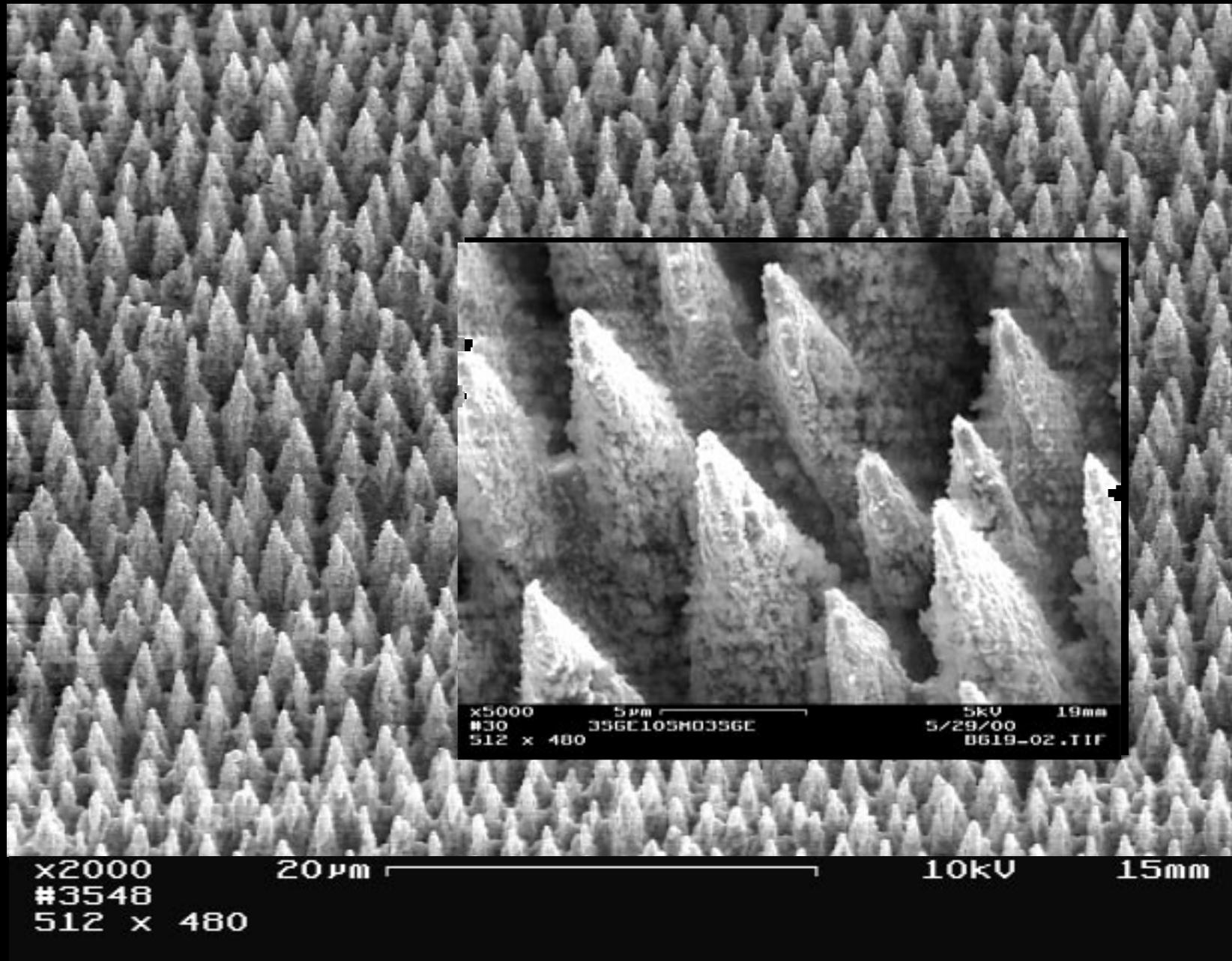
10 μm

SKU 19mm
5/29/00
B619-01.TIF

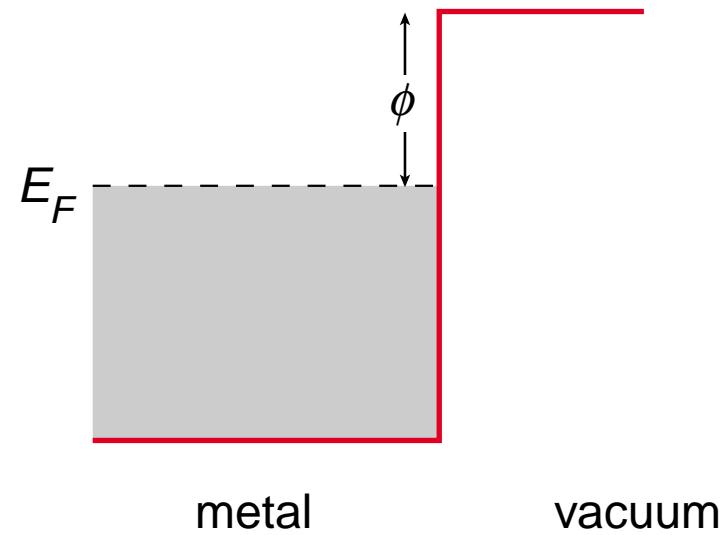
10kV

15mm

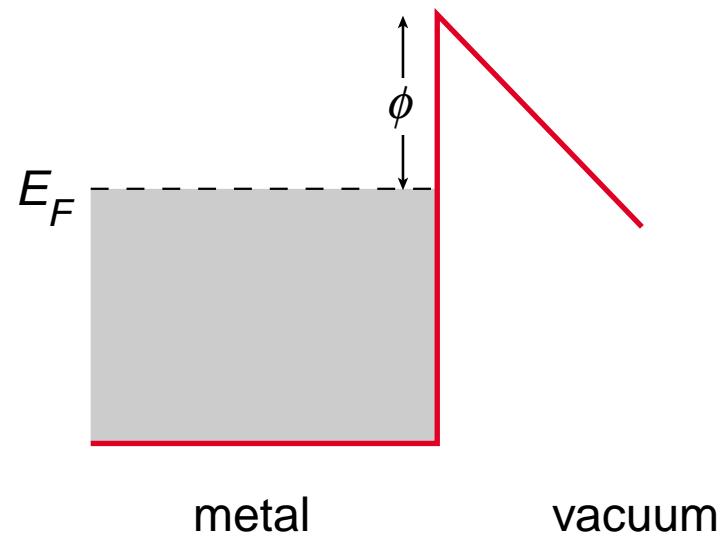




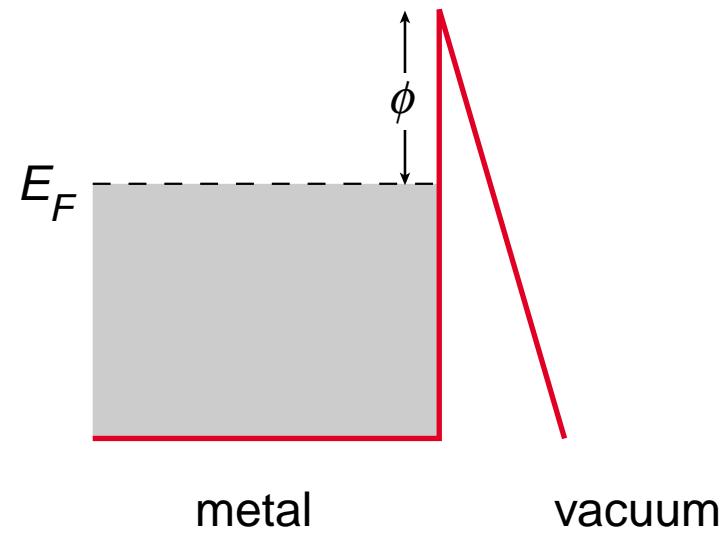
Field emission



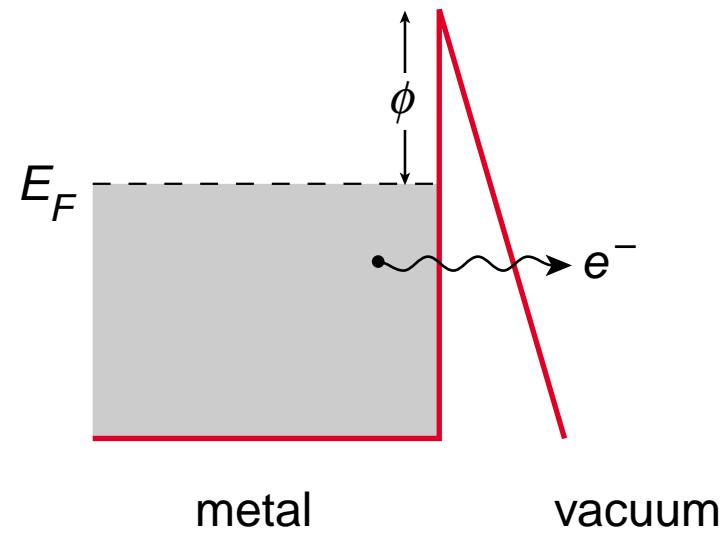
Field emission



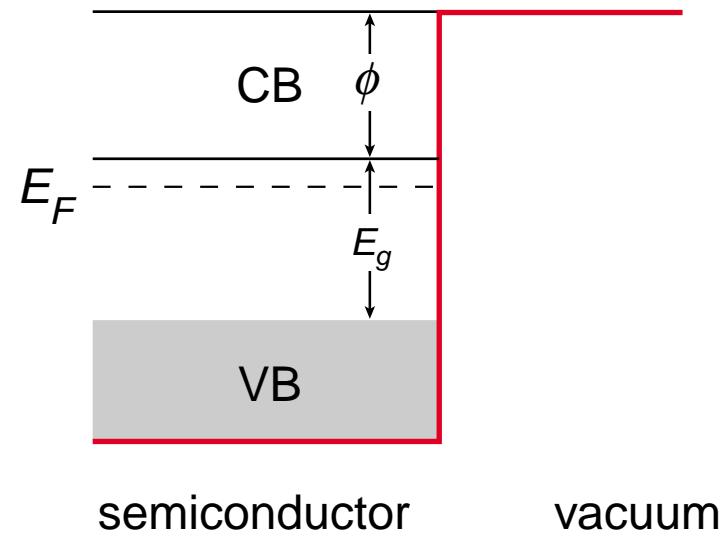
Field emission



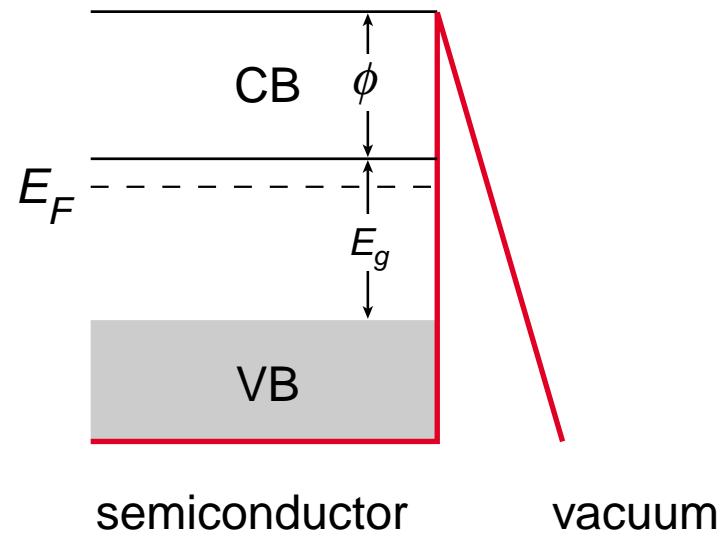
Field emission



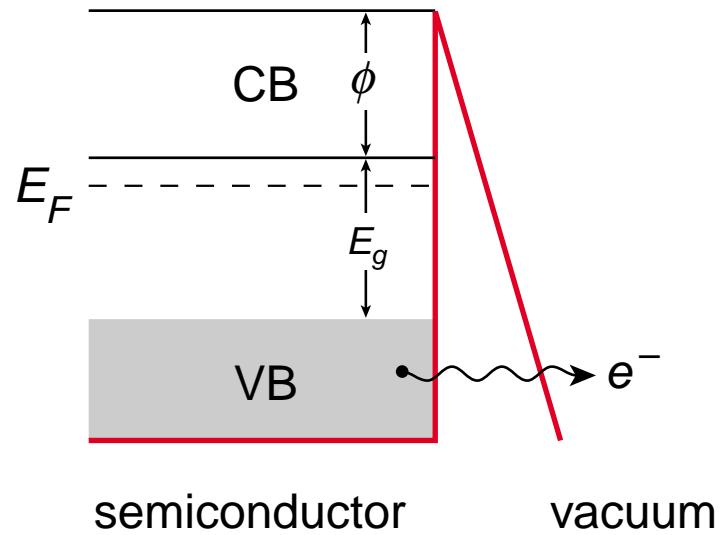
Field emission



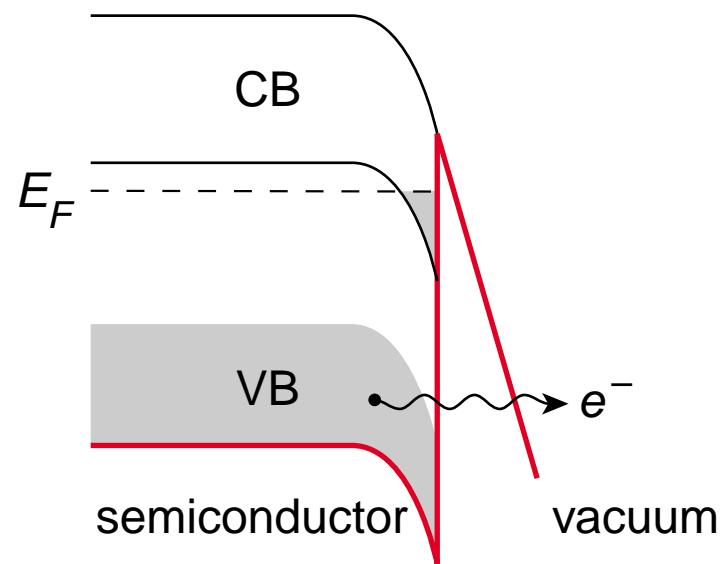
Field emission



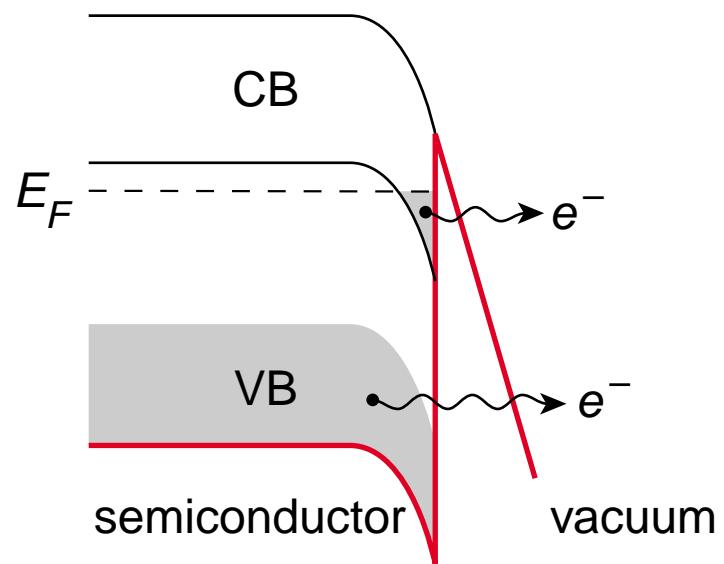
Field emission



Field emission

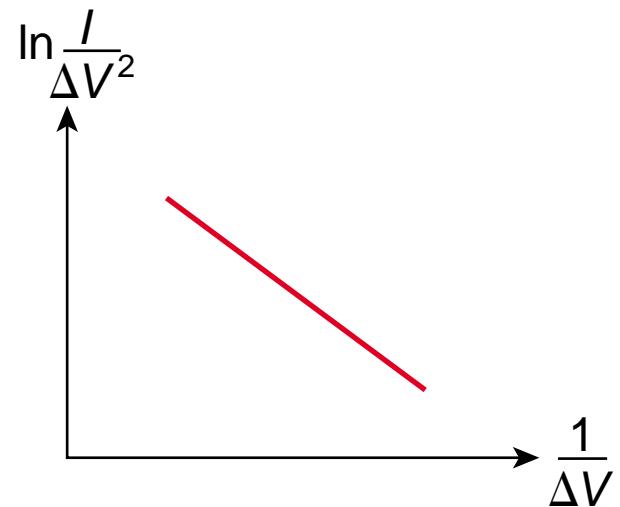


Field emission



Field emission

$$\ln \frac{I}{\Delta V^2} = \ln a - b \frac{1}{\Delta V}$$



R.H. Fowler and L. Nordheim, *Proc. R. Soc. Lond. A* (1928)

Setup



Setup



gold coating

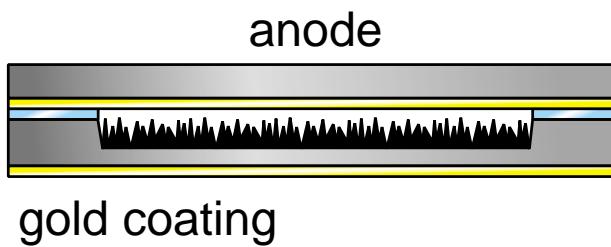
Setup

20 μm mica spacers

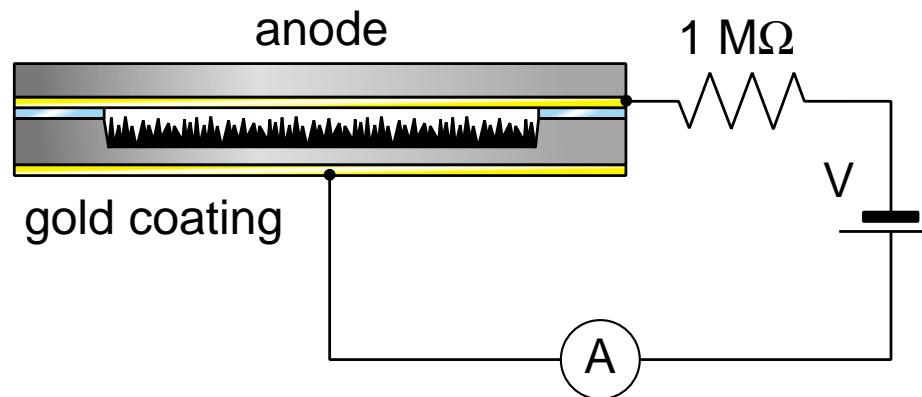


gold coating

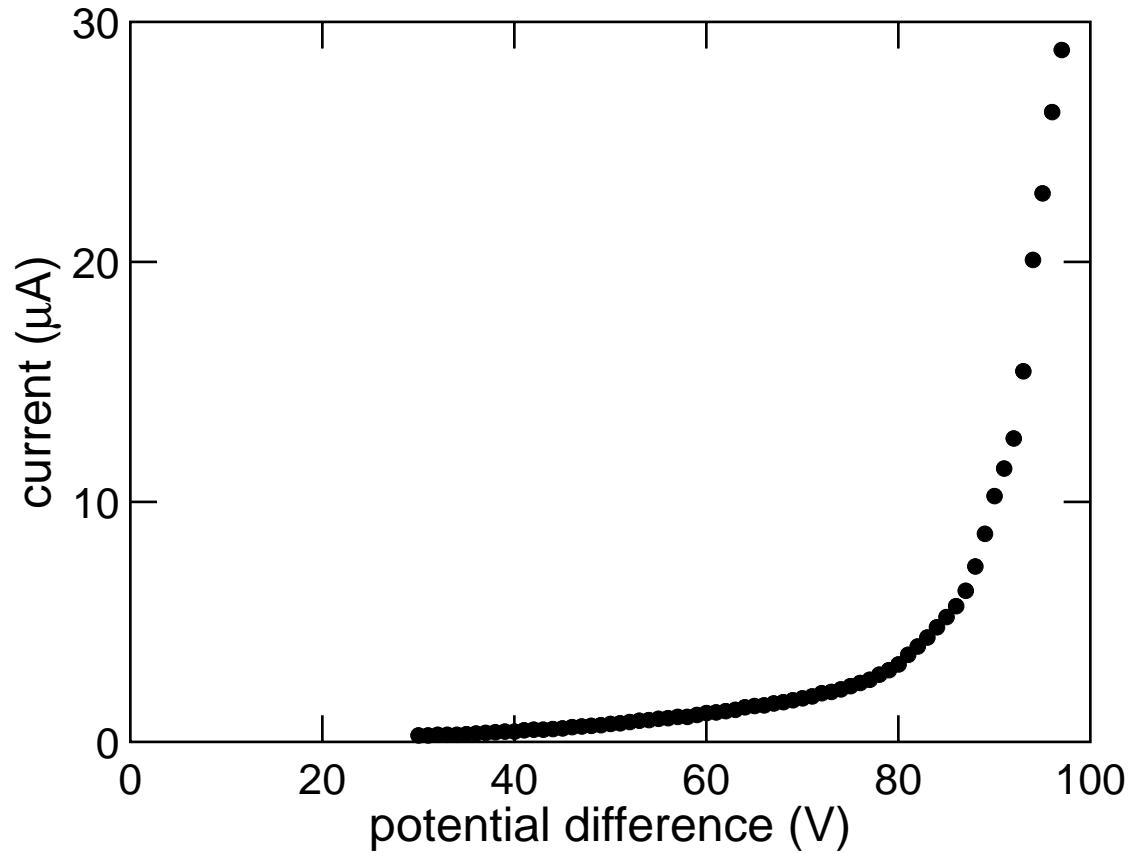
Setup



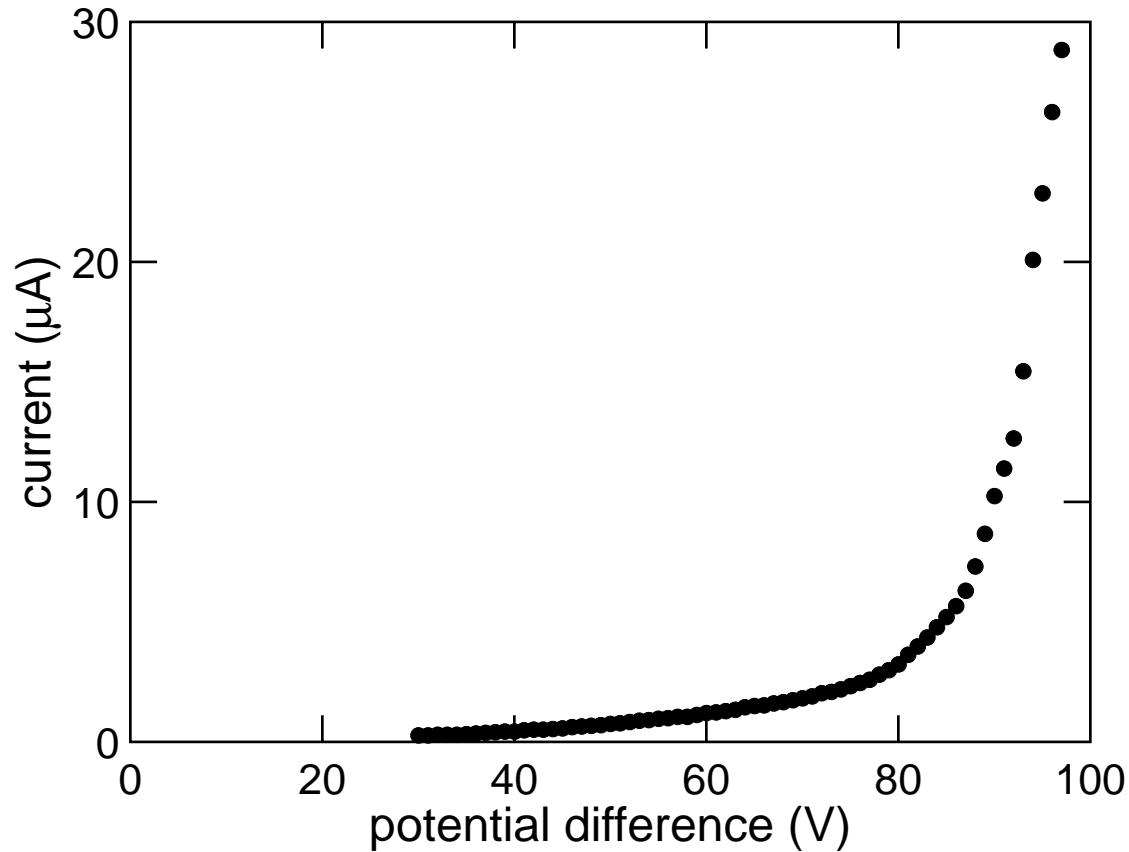
Setup



Results

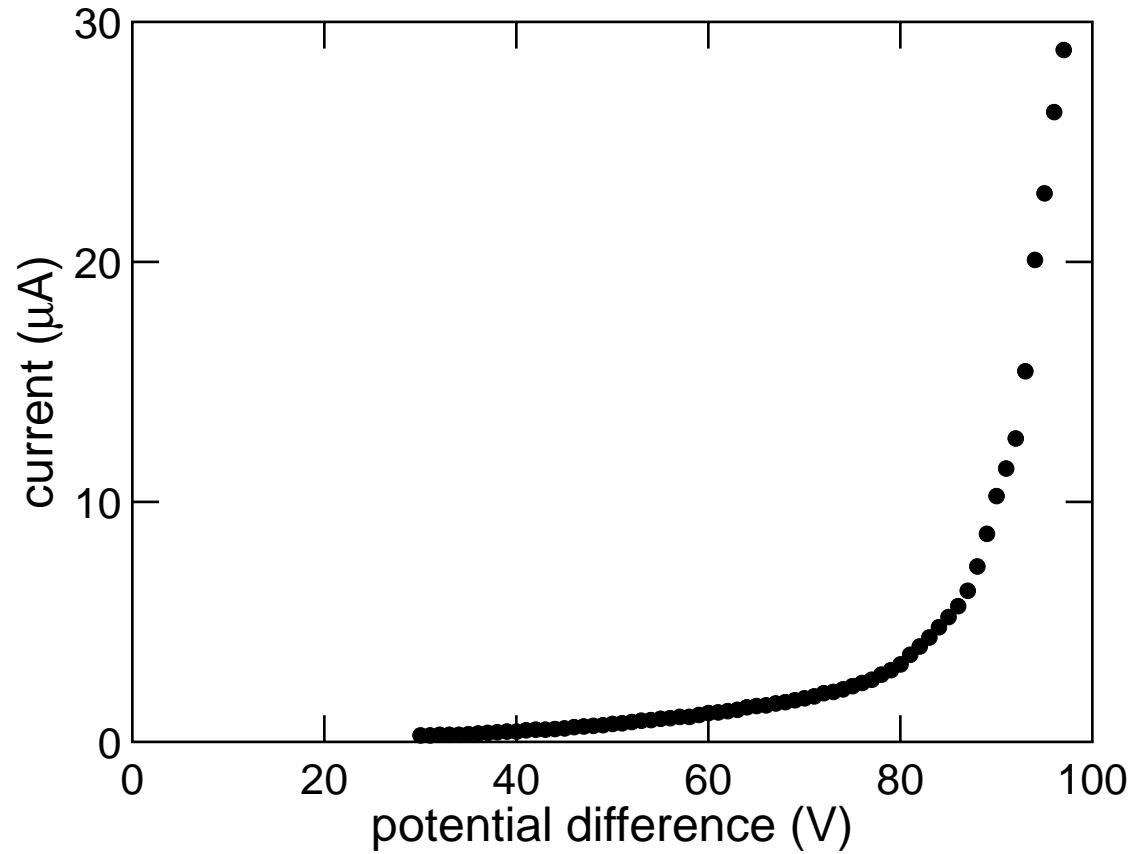


Results



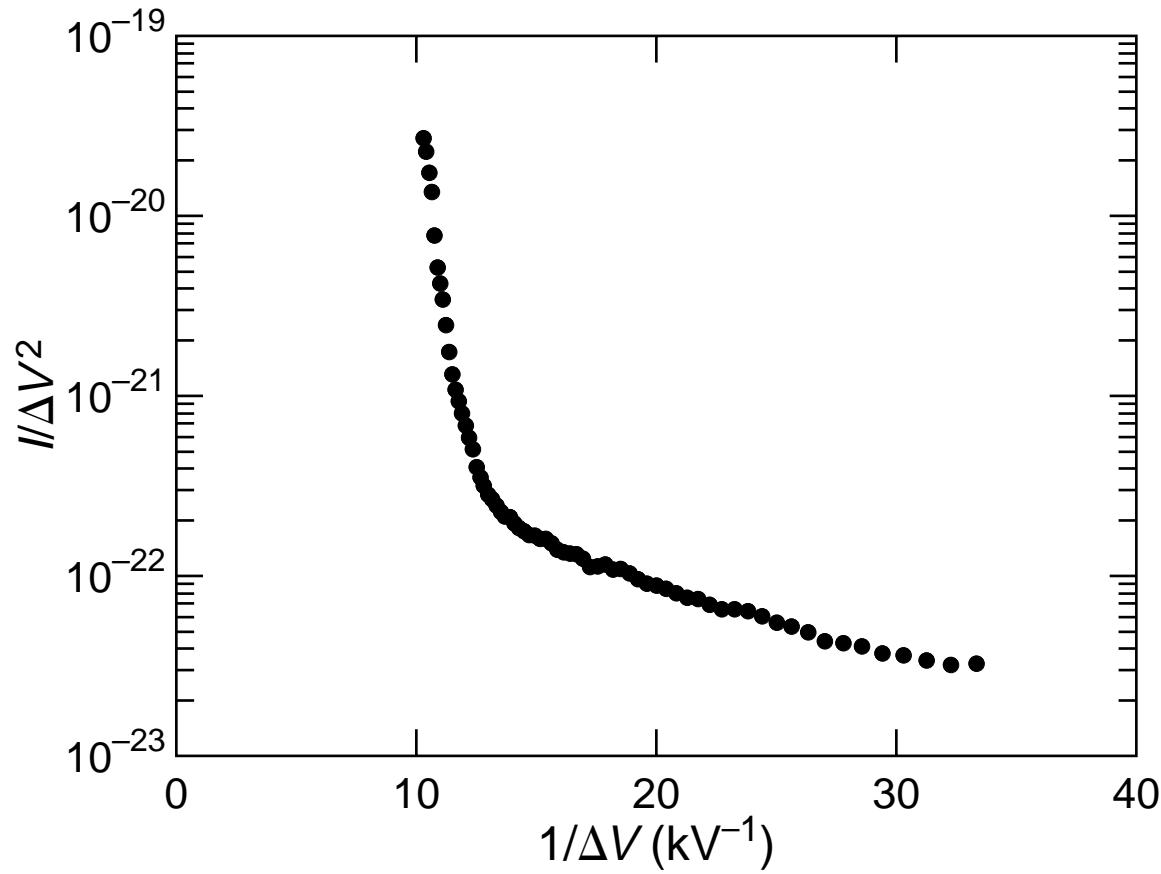
turn-on field (1 $\mu\text{A}/\text{cm}^2$): 1.3 V/ μm

Results

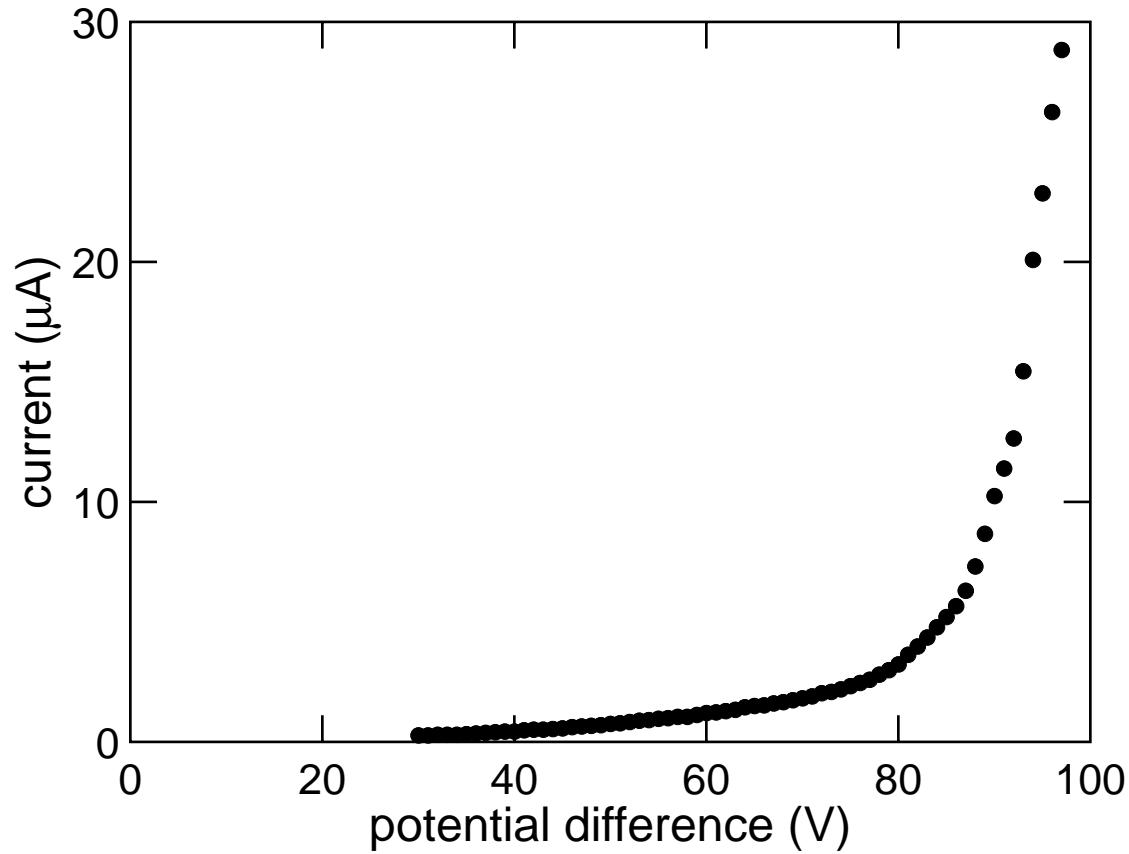


threshold field ($10 \mu\text{A}/\text{cm}^2$): $2.15 \text{ V}/\mu\text{m}$

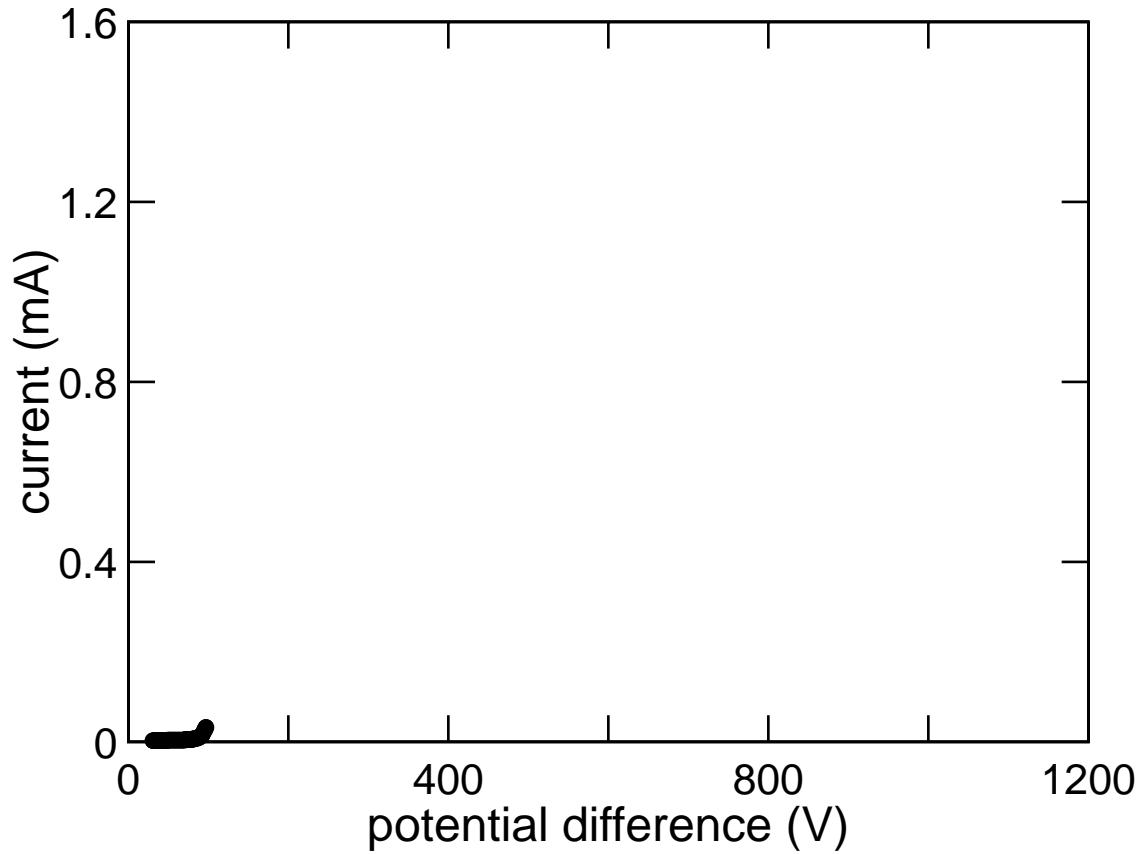
Results



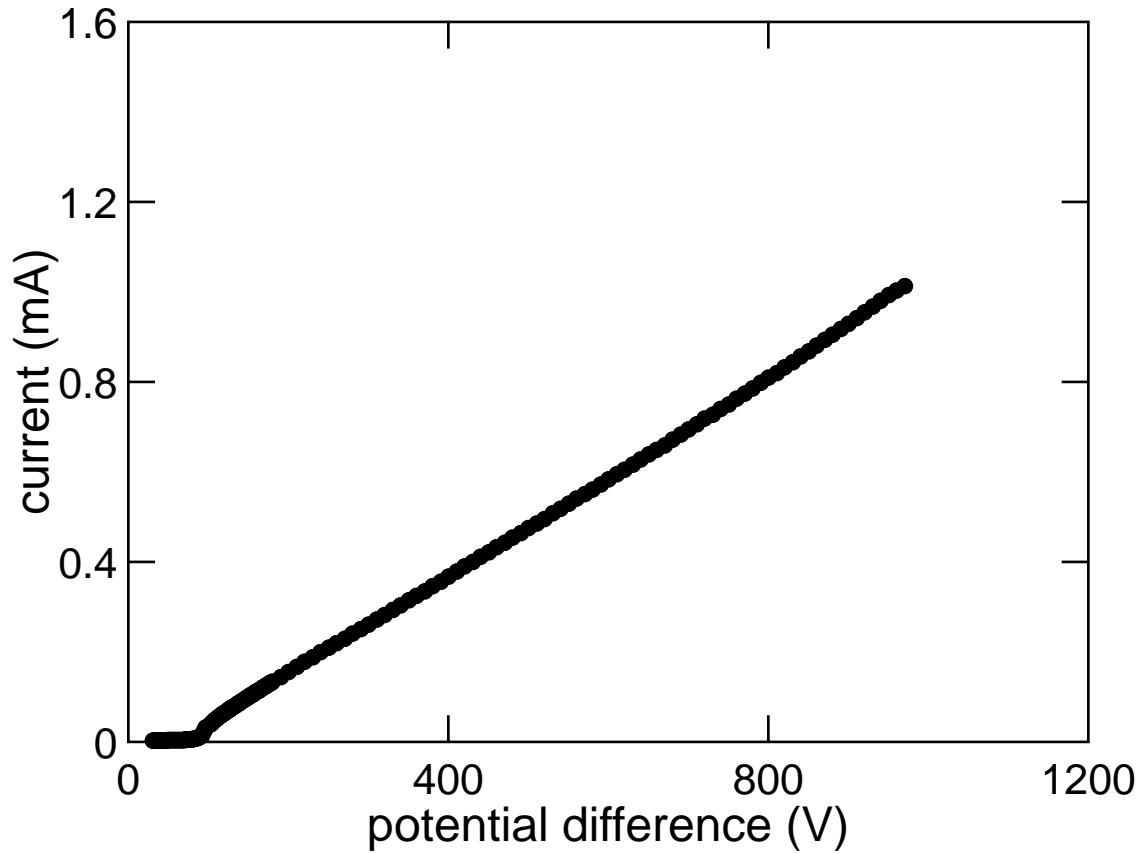
Results



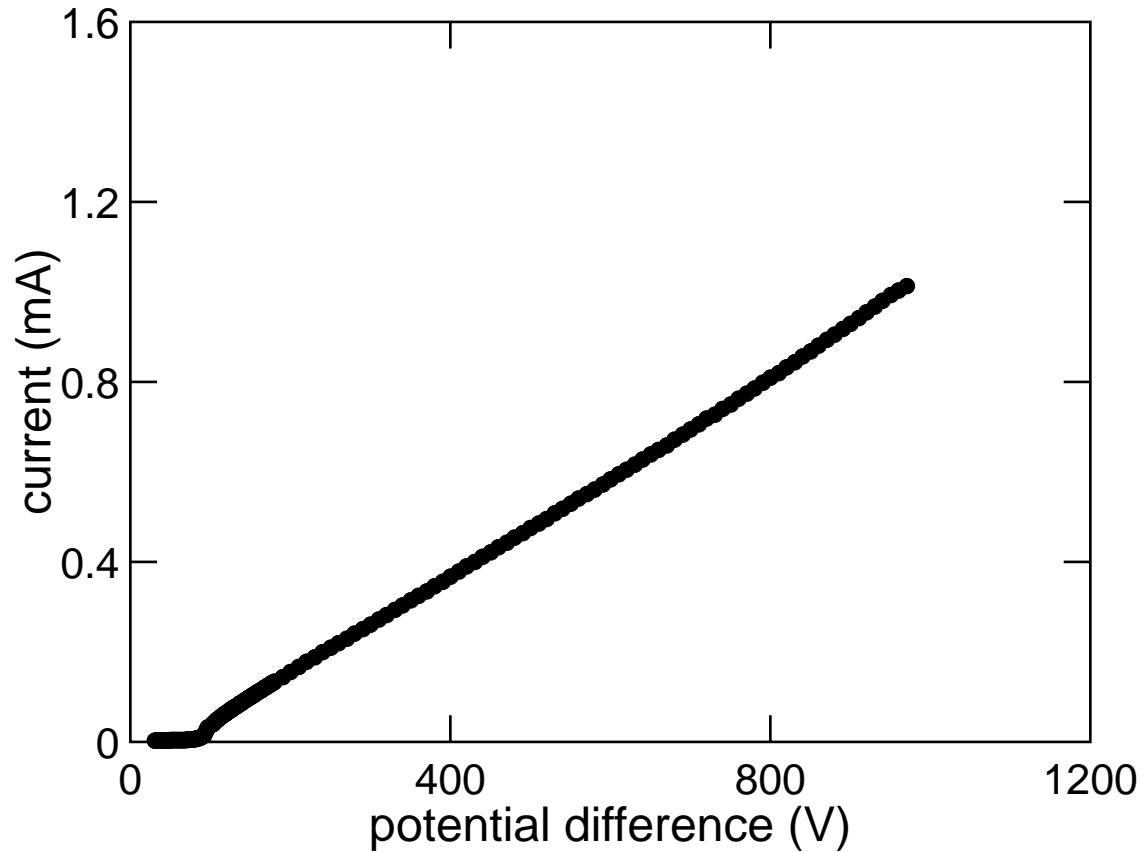
Results



Results

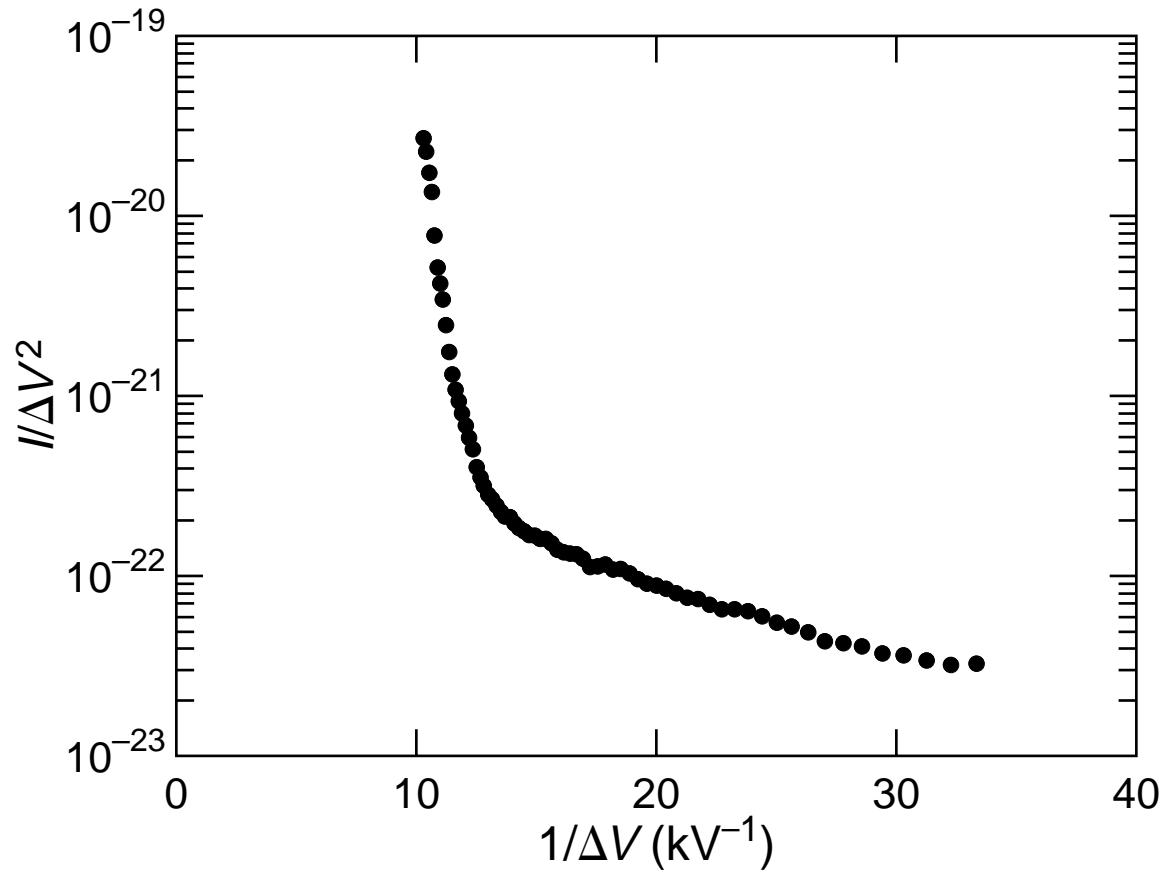


Results

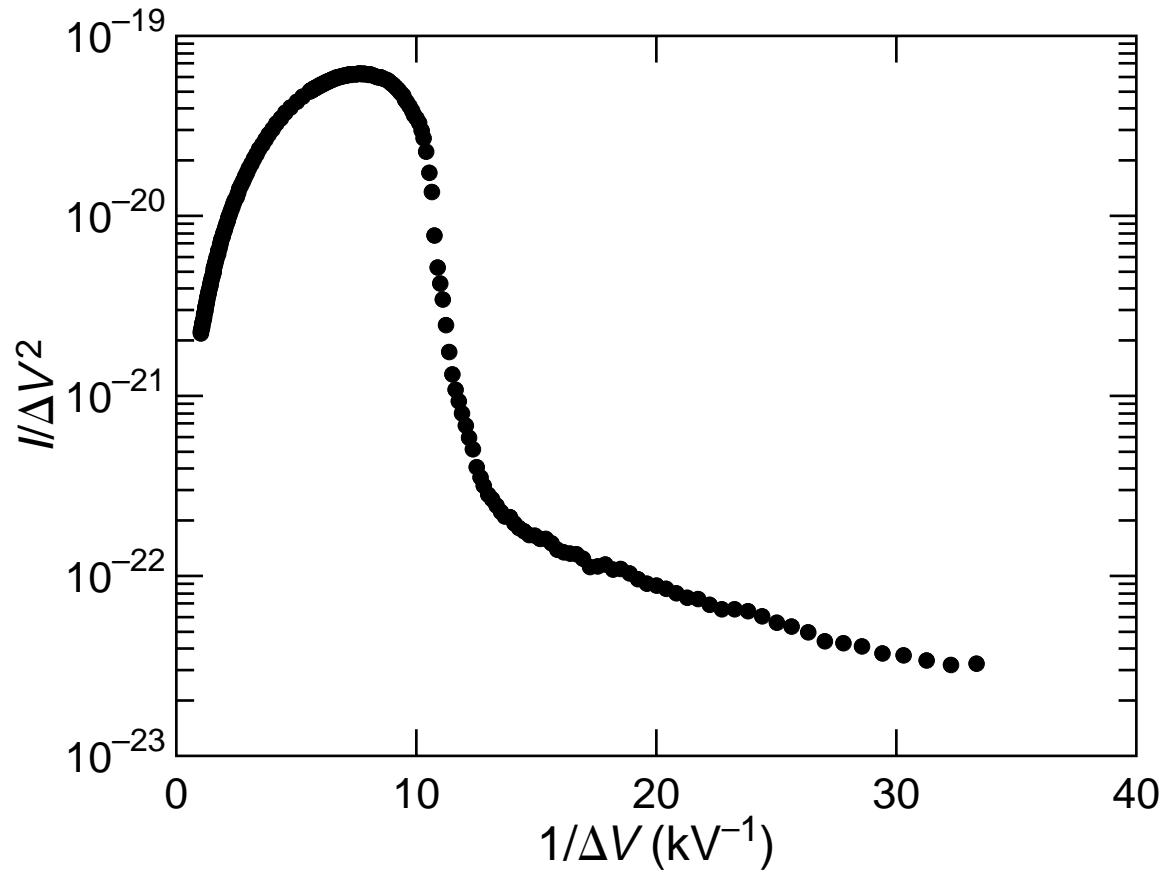


maximum current: 2 mA (4 mm² sample)

Results



Results



Discussion

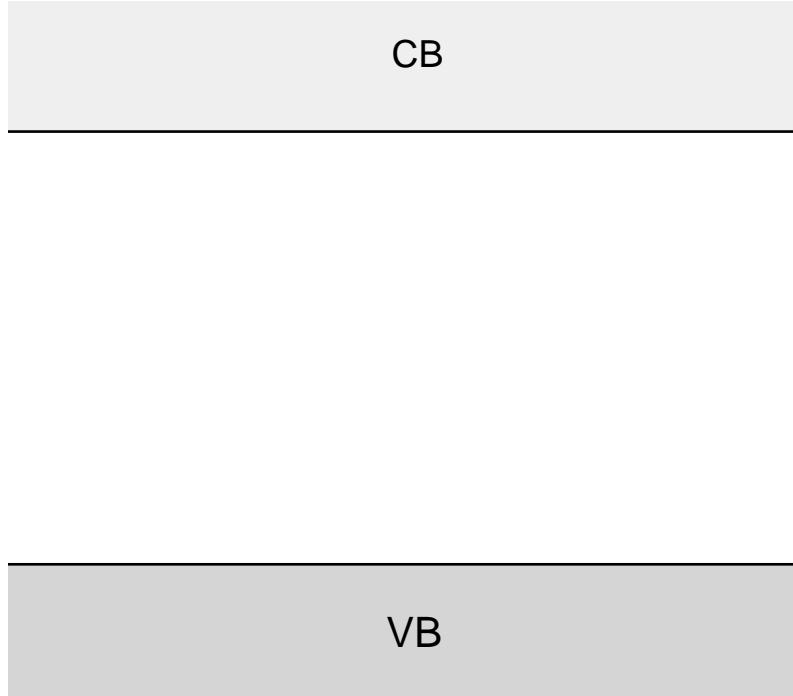
Secondary ion mass spectrometry:

- ▶ 10^{20} cm^{-3} sulfur

- ▶ 10^{17} cm^{-3} fluorine

Discussion

sulfur introduces states in the gap



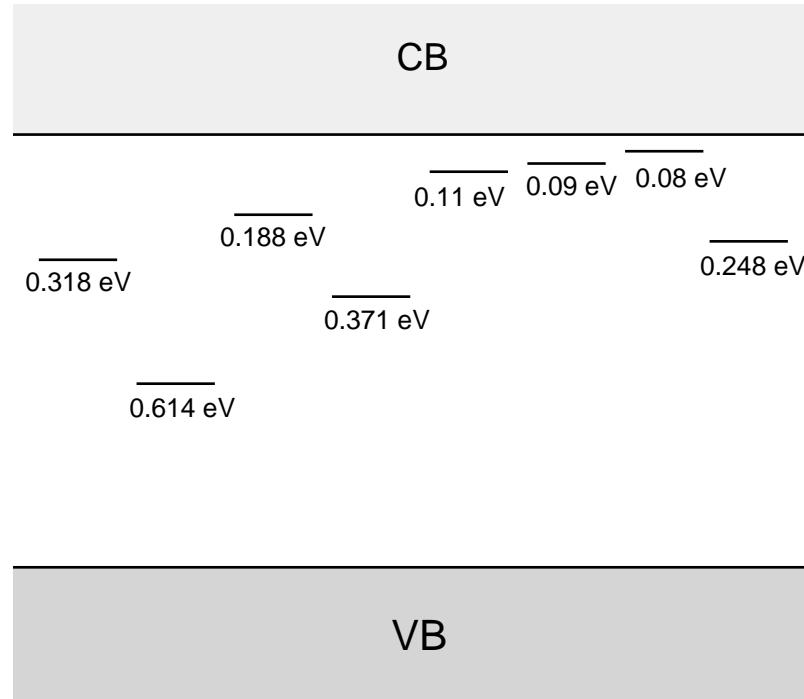
CB

A diagram illustrating the electronic structure of a material. It features two horizontal grey bars representing energy bands. The top bar is labeled "CB" (Conduction Band) and the bottom bar is labeled "VB" (Valence Band). A thin black horizontal line separates the two bars, representing the energy gap. The entire diagram is set against a white background.

VB

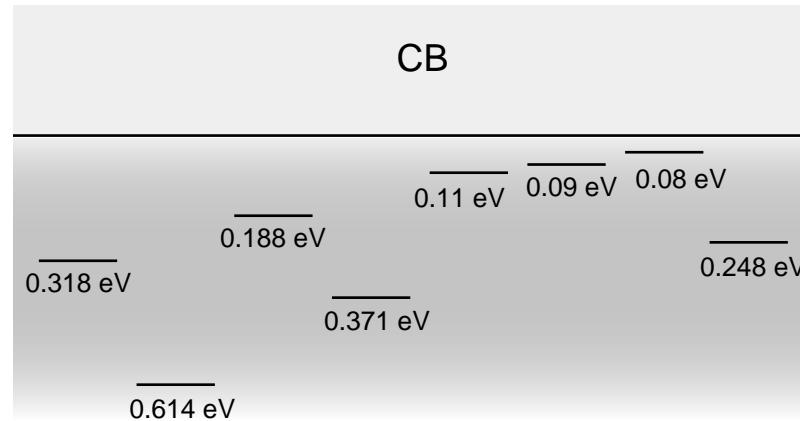
Discussion

sulfur introduces states in the gap



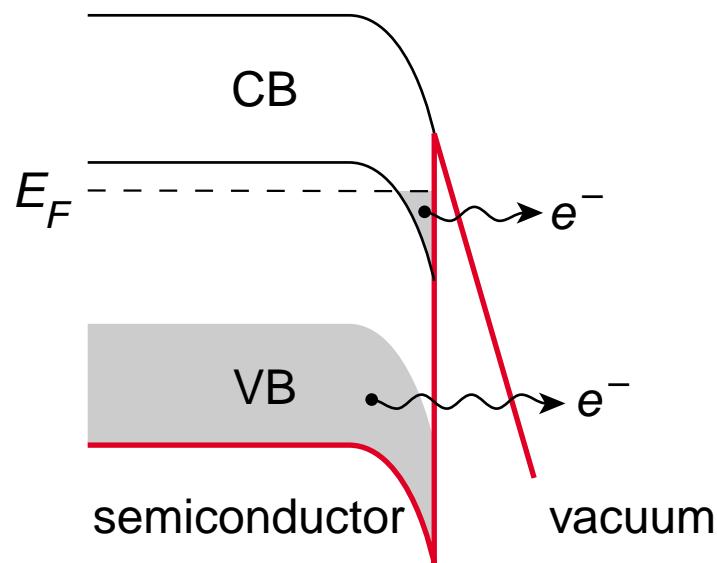
Discussion

states broaden into a band



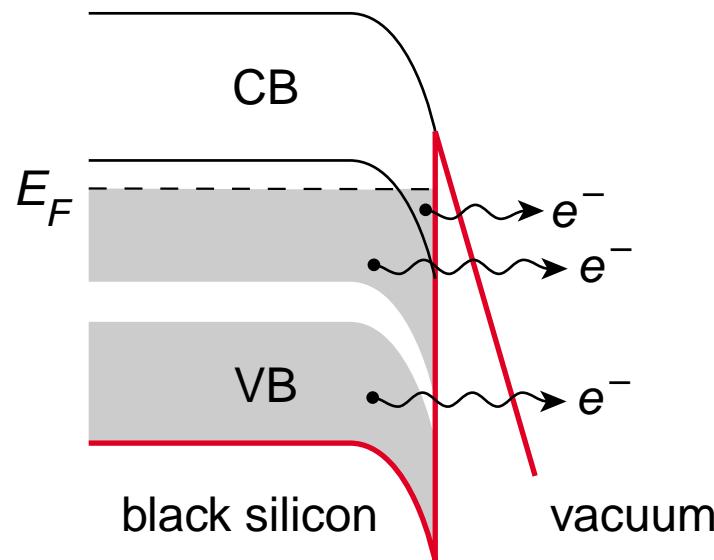
VB

Discussion



Discussion

sulfur band provides additional electrons



Summary

Microstructured silicon

- ▶ **fabricated by simple, maskless process**

Summary

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- ▶ **can be integrated with microelectronics**

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Microstructured silicon

- ▶ **fabricated by simple, maskless process**
- ▶ **can be integrated with microelectronics**
- ▶ **provides stable, high field-emission current**

Summary

Microstructured silicon

- ▶ **fabricated by simple, maskless process**
- ▶ **can be integrated with microelectronics**
- ▶ **provides stable, high field-emission current**
- ▶ **is durable**

Funding: Army Research Office
Department of Energy
NDSEG

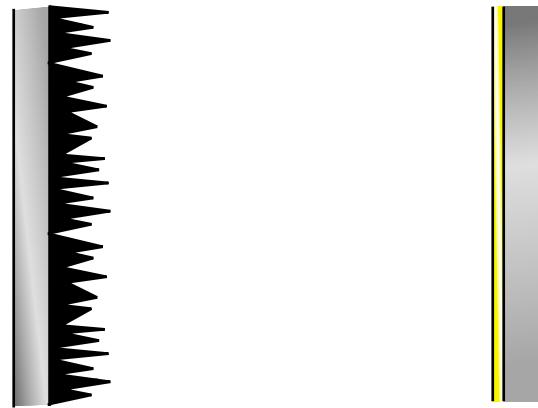


Acknowledgments:
Prof. Mike Aziz (Harvard University)

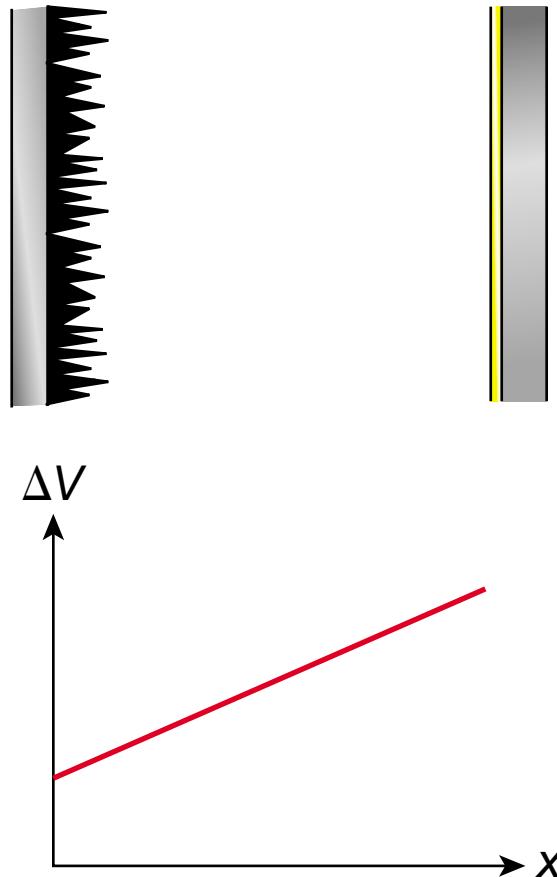
For a copy of this talk and
additional information, see

<http://mazur-www.harvard.edu>

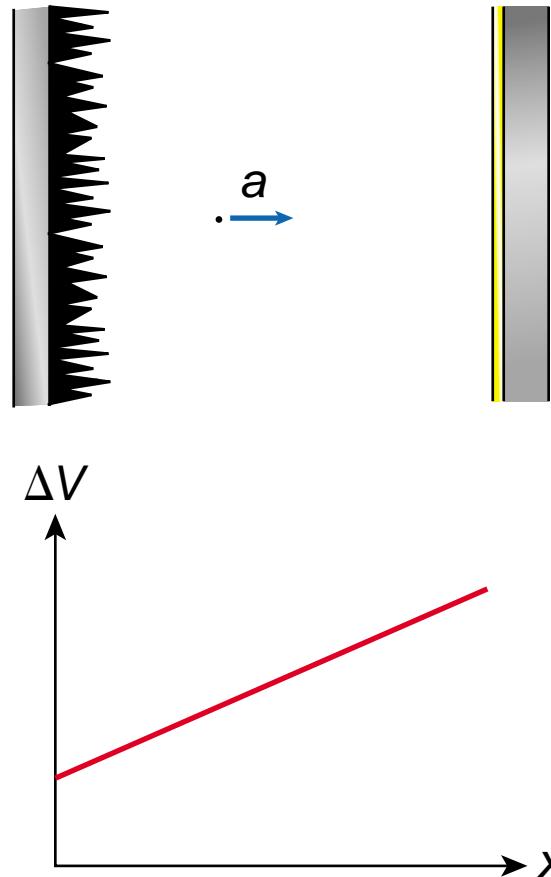
Space charge effect



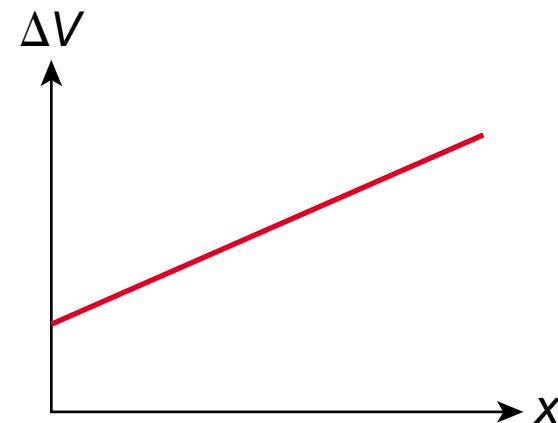
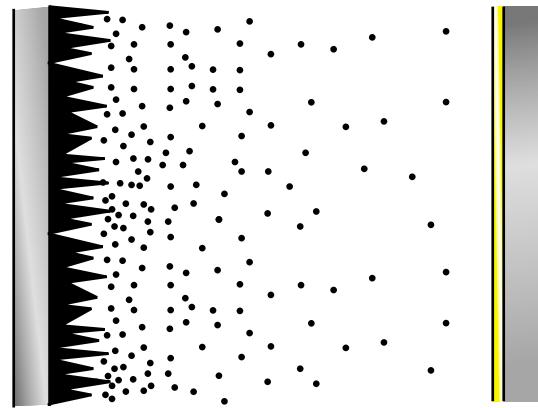
Space charge effect



Space charge effect



Space charge effect



Space charge effect

